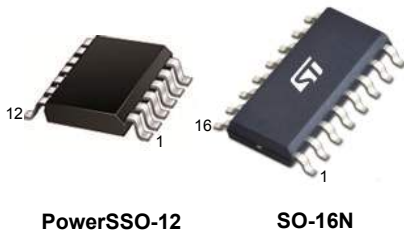


Double channel high-side driver with analog current sense for 24 V automotive applications




PowerSSO-12

SO-16N

Features

Description	Parameter	Value
Max. transient supply voltage	V_{CC}	58 V
Operating voltage range	V_{CC}	8 to 36 V
Typ. on-state resistance (per channel)	R_{ON}	100 m Ω
Current limitation (typ.)	I_{LIM}	22 A
Off-state supply current	I_S	2 μ A ⁽¹⁾

1. Typical value with all loads connected.

- AEC-Q100 qualified 
- General
 - Very low standby current
 - 3.0 V CMOS compatible input
 - Optimized electromagnetic emission
 - Very low electromagnetic susceptibility
 - Compliant with European directive 2002/95/EC
 - Fault reset standby pin (FR_Stby)
 - Optimized for LED application
- Diagnostic functions
 - Proportional load current sense
 - High current sense precision for wide range currents
 - Off-state openload detection
 - Output short to V_{CC} detection
 - Overload and short to ground latch-off
 - Thermal shutdown latch-off
 - Very low current sense leakage
- Protections
 - Undervoltage shutdown
 - Overvoltage clamp
 - Load current limitation
 - Self limiting of fast thermal transients
 - Protection against loss of ground and loss of V_{CC}
 - Thermal shutdown
 - Electrostatic discharge protection

Product status links

[VND5T100LAJ-E](#)
[VND5T100LAS-E](#)

Applications

- All types of resistive, inductive and capacitive loads

Description

The VND5T100LAJ-E and VND5T100LAS-E are monolithic devices made using STMicroelectronics VIPower technology, intended for driving resistive or inductive loads with one side connected to the ground. Active V_{CC} pin voltage clamp protects the device against low energy spikes.

These devices integrate an analog current sense, which delivers a current proportional to the load current.

Fault conditions such as overload, overtemperature, or short to V_{CC} are reported via the current sense pin.

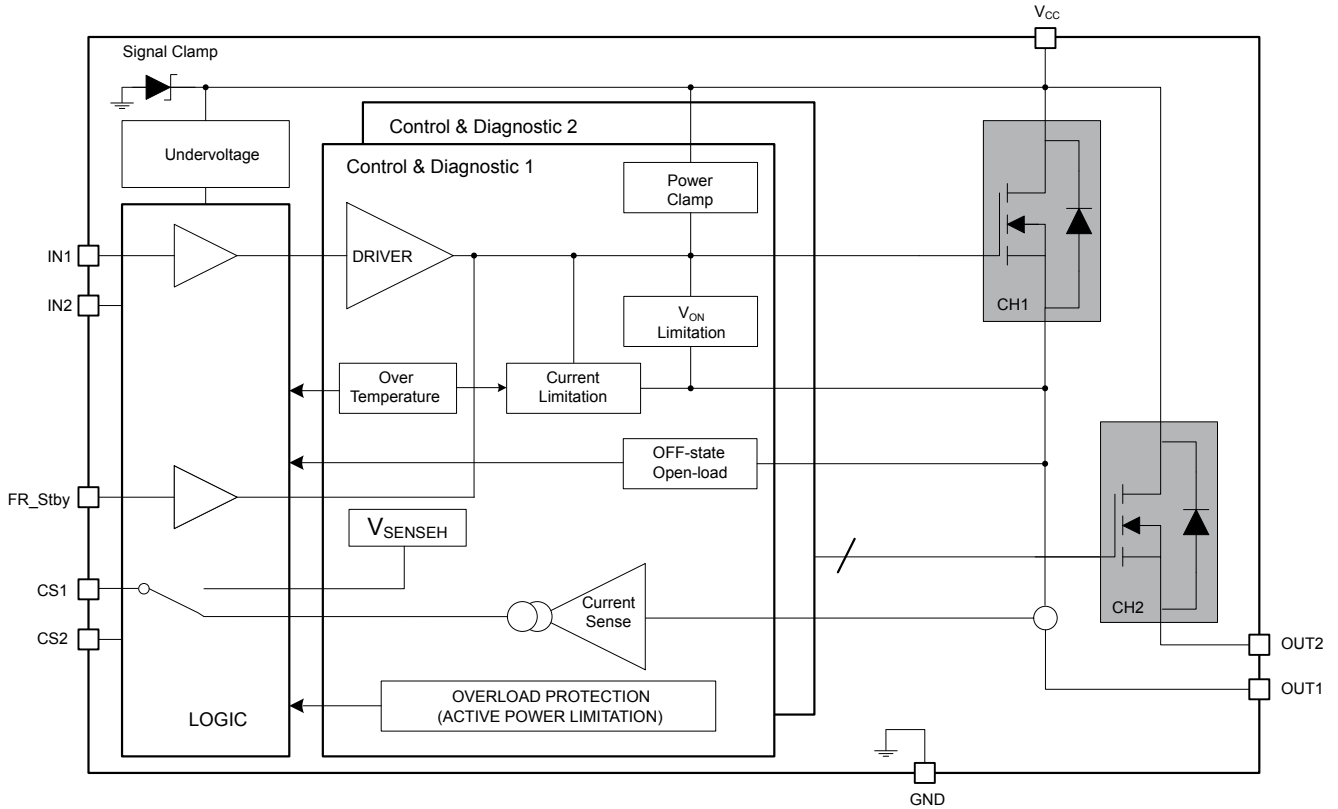
Output current limitation protects the devices in overload conditions. The device latches off in case of overload or thermal shutdown.

The devices are reset by a low level pass on the fault reset standby pin.

A permanent low level on the inputs and on the fault reset standby pin disables all outputs and sets the device in standby mode.

1 Block diagram and pin description

Figure 1. Block diagram

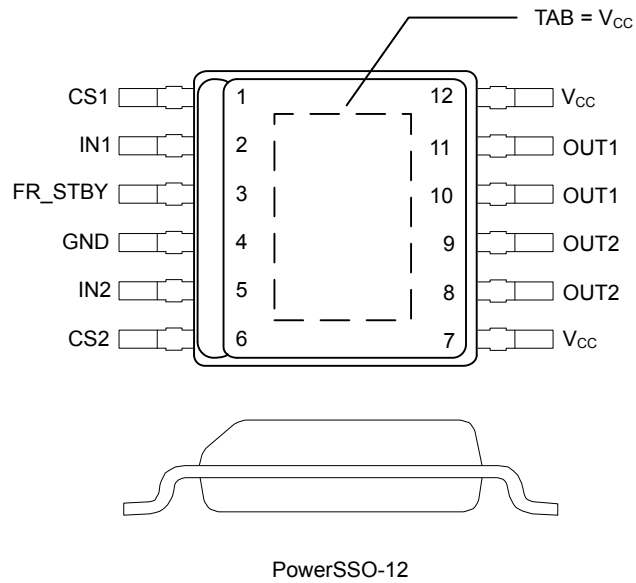


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Table 1. Pin function

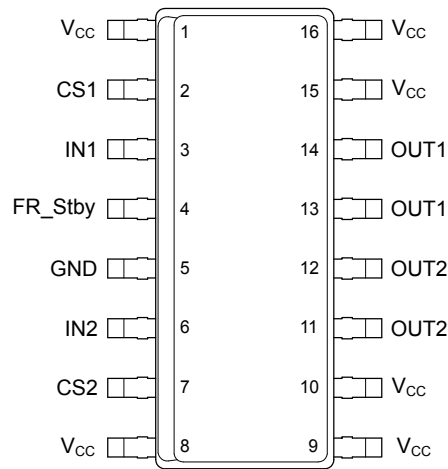
Name	Function
V _{CC}	Battery connection.
OUT1, 2	Power outputs.
GND	Ground connection.
IN1, 2	Voltage controlled input pins with hysteresis, CMOS compatible. They control output switch state.
CS1, 2	Analog current sense pins, they deliver a current proportional to the load current.
FR_Stby	In case of latch-off for overtemperature/overcurrent condition, a low pulse on the FR_Stby pin is needed to reset the channel. The device enters in standby mode if all inputs and the FR_Stby pin are low.

Figure 2. Configuration diagram PowerSSO-12 (top view)



GAPGCF000109

Figure 3. Configuration diagram SO-16N (top view)



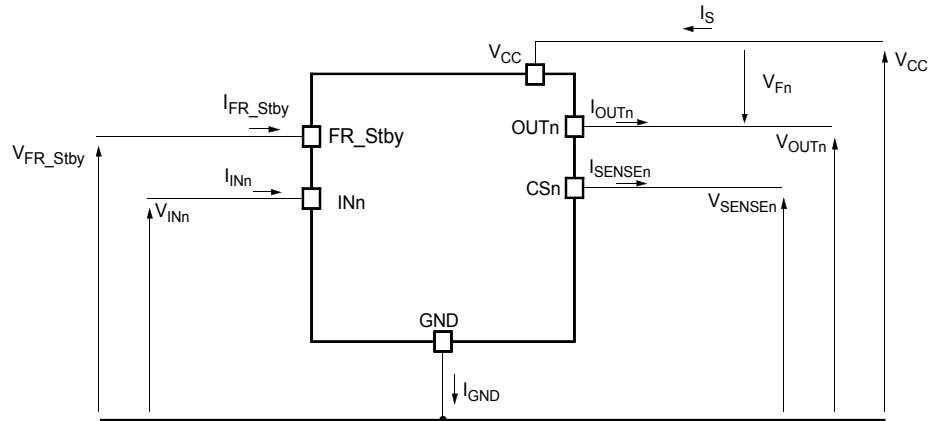
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Table 2. Suggested connections for unused and not connected pins

Connection/pin	CurrentSense	NC	Output	Input	FR_Stby
Floating	Not allowed	X ⁽¹⁾	X	X	X
To ground	Through 10 kΩ resistor	X	Not allowed	Through 10 kΩ resistor	Through 10 kΩ resistor

1. X: do not care.

2 Electrical specification

Figure 4. Current and voltage conventions


GAPGCF00195_v2

2.1 Absolute maximum ratings

Stressing the device above the ratings listed in the [Table 3](#) may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to the conditions reported in this section for extended periods may affect device reliability.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V_{CC}	DC supply voltage	58	V	
$-V_{CC}$	Reverse DC supply voltage	0.3	V	
$-I_{GND}$	DC reverse ground pin current	200	mA	
I_{OUT}	DC output current	Internally limited	A	
$-I_{OUT}$	Reverse DC output current	20	A	
I_{IN}	DC input current	-1 to 10	mA	
I_{FR_Stby}	Fault reset standby DC input current	-1 to 1.5	mA	
$-I_{CSENSE}$	DC reverse CS pin current	200	mA	
V_{CSENSE}	Current sense maximum voltage	$(V_{CC} - 58)$ to V_{CC}	V	
E_{MAX}	Maximum switching energy ($L = 1.9$ mH; $V_{BAT} = 32$ V; $T_{Jstart} = 150$ °C; $I_{OUT} = I_{limL}$ (typ.))	70	mJ	
L_{smax}	Maximum stray inductance in short circuit condition $R_L = 300$ mΩ, $V_{BAT} = 32$ V, $T_{Jstart} = 150$ °C, $I_{OUT} = I_{limH}$ (max.)	40	μH	
V_{ESD}	Electrostatic discharge (human body model: $R = 1.5$ kΩ, $C = 100$ pF)	IN1, 2	4000	V
		CS1, 2	2000	
		FR_Stby	4000	
		OUT1, 2	5000	
		V_{CC}	5000	
V_{ESD}	Charge device model (CDM-AEC-Q100-011)	750	V	
T_J	Junction operating temperature	-40 to 150	°C	

Symbol	Parameter	Value	Unit
T _{stg}	Storage temperature	-55 to 150	°C

2.2 Thermal data

Table 4. Thermal data

Symbol	Parameter	Maximum value		Unit
		PowerSSO-12	SO-16N	
R _{thJC}	Thermal resistance, junction-to-case (with one channel ON)	6		°C/W
R _{thJP}	Thermal resistance junction-pin (with one channel ON)		26	°C/W
R _{thJA}	Thermal resistance, junction-to-ambient	See Figure 28	See Figure 32	°C/W

2.3 Electrical characteristics

8 V < V_{CC} < 36 V, -40 °C < T_J < 150 °C, unless otherwise specified.

Table 5. Power section

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{CC}	Operating supply voltage		8	24	36	V
V _{USD}	Undervoltage shutdown			3.5	5	V
V _{USDhyst}	Undervoltage shutdown hysteresis			0.5		V
R _{ON}	On-state resistance ⁽¹⁾	I _{OUT} = 1.5 A, T _J = 25 °C		100		mΩ
		I _{OUT} = 1.5 A, T _J = 150 °C			200	
V _{clamp}	Clamp voltage	I _S = 20 mA	58	64	70	V
I _S	Supply current	Off-state, V _{CC} = 24 V, T _J = 25 °C, V _{IN} = V _{OUT} = V _{SENSE} = 0 V, V _{FR_Stby} = 0 V		2 ⁽²⁾	5 ⁽²⁾	μA
		On-state, V _{CC} = 24 V, V _{IN} = 5 V, I _{OUT} = 0 A		4.2	6	mA
I _{L(off)}	Off-state output current	V _{IN} = V _{OUT} = 0 V, V _{CC} = 24 V, T _J = 25 °C	0	0.01	3	μA
		V _{IN} = V _{OUT} = 0 V, V _{CC} = 24 V, T _J = 125 °C	0		5	
V _F	Output - V _{CC} diode voltage	-I _{OUT} = 1.5 A, T _J = 150 °C			0.7	V

1. For each channel.
2. Power MOSFET leakage included.

Table 6. Switching (V_{CC} = 24 V, T_J = 25 °C)

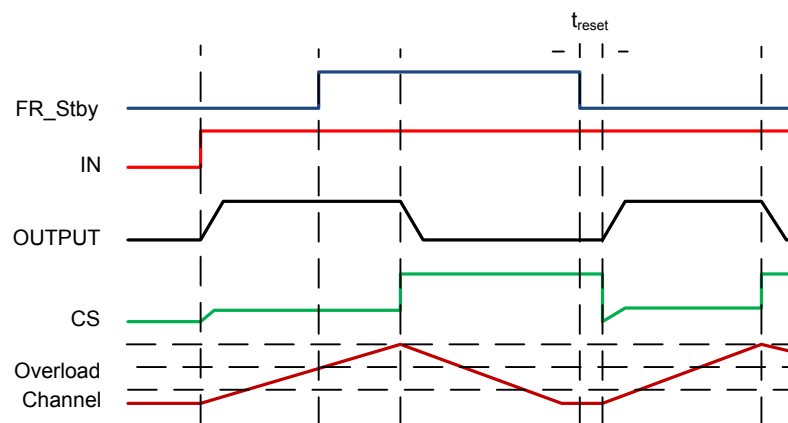
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	R _L = 16 Ω		27		μs
t _{d(off)}	Turn-off delay time	R _L = 16 Ω		38		μs
(dV _{OUT} /dt) _(on)	Turn-on voltage slope	R _L = 16 Ω		1		V/μs
(dV _{OUT} /dt) _(off)	Turn-off voltage slope	R _L = 16 Ω		0.65		V/μs
W _{ON}	Switching energy losses during t _{won}	R _L = 16 Ω		0.23		mJ
W _{OFF}	Switching energy losses during t _{woff}	R _L = 16 Ω		0.26		mJ

Table 7. Logic inputs

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{IL}	Input low level voltage				0.9	V
I _{IL}	Low level input current	V _{IN} = 0.9 V	1			μA
V _{IH}	Input high level voltage		2.1			V
I _{IH}	High level input current	V _{IN} = 2.1 V			10	μA
V _{I(hyst)}	Input hysteresis voltage		0.25			V

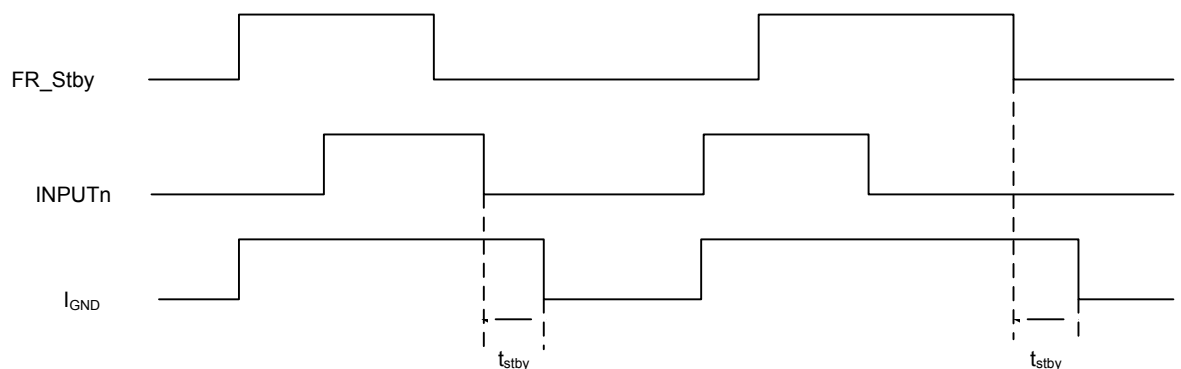
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{ICL}	Input clamp voltage	$I_{IN} = 1 \text{ mA}$	5.5		7	V
		$I_{IN} = -1 \text{ mA}$		-0.7		
$V_{FR_Stby_L}$	Fault_reset_standby low level voltage				0.9	V
$I_{FR_Stby_L}$	Low level fault_reset_standby current	$V_{FR_Stby} = 0.9 \text{ V}$	1			μA
$V_{FR_Stby_H}$	Fault_reset_standby high level voltage		2.1			V
$I_{FR_Stby_H}$	High level fault_reset_standby current	$V_{FR_Stby} = 2.1 \text{ V}$			10	μA
$V_{FR_Stby(hyst)}$	Fault_reset_standby hysteresis voltage		0.25			V
$V_{FR_Stby_CL}$	Fault_reset_standby clamp voltage	$I_{FR_Stby} = 15 \text{ mA} (t < 10 \text{ ms})$	11		15	V
		$I_{FR_Stby} = -1 \text{ mA}$		-0.7		V
t_{reset}	Overload latch-off reset time	See Figure 5	2		24	μs
t_{stby}	Standby delay	See Figure 6	120		1200	μs

Figure 5. t_{reset} definition



GAPGCFT000112

Figure 6. t_{stby} definition



GAPGCFT000111_v2

Table 8. Protections and diagnostics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{limH}	DC short circuit current	$V_{CC} = 24\text{ V}$	16	22	30	A
		$5\text{ V} < V_{CC} < 36\text{ V}$			30	
I_{limL}	Short circuit current during thermal cycling	$V_{CC} = 24\text{ V}, T_R < T_J < T_{TSD}$		6		A
T_{TSD}	Shutdown temperature		150	175	200	°C
T_R	Reset temperature		$T_{RS} + 1$	$T_{RS} + 5$		°C
T_{RS}	Thermal reset of status		135			°C
T_{HYST}	Thermal hysteresis ($T_{TSD} - T_R$)			7		°C
V_{DEMAG}	Turn-off output voltage clamp	$I_{OUT} = 1.5\text{ A}, V_{IN} = 0\text{ V}, L = 6\text{ mH}$	$V_{CC} - 58$	$V_{CC} - 64$	$V_{CC} - 70$	V
V_{ON}	Output voltage drop limitation	$I_{OUT} = 50\text{ A}, T_J = -40\text{ °C to }150\text{ °C}$		25		mV

Table 9. Current sense (8 V < V_{CC} < 36 V)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
K_{OL}	I_{OUT}/I_{SENSE}	$I_{OUT} = 12\text{ mA}, V_{SENSE} = 0.5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	833			
K_{LED}	I_{OUT}/I_{SENSE}	$I_{OUT} = 50\text{ mA}, V_{SENSE} = 0.5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1328	2190	3332	
$dK_{LED}/K_{LEDTOT}^{(1)}$	Current sense ratio drift	$I_{OUT} = 12\text{ mA to }25\text{ mA}, I_{CAL} = 18\text{ mA}, V_{SENSE} = 0.5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-30		30	%
K_0	I_{OUT}/I_{SENSE}	$I_{OUT} = 100\text{ mA}, V_{SENSE} = 0.5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1170	1950	2730	
$dK_0/K_0^{(1)}$	Current sense ratio drift	$I_{OUT} = 100\text{ mA}, V_{SENSE} = 0.5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-18		18	%
K_1	I_{OUT}/I_{SENSE}	$I_{OUT} = 0.4\text{ A}, V_{SENSE} = 1\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1259	1740	2191	
$dK_1/K_1^{(1)}$	Current sense ratio drift	$I_{OUT} = 0.4\text{ A}, V_{SENSE} = 1\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-15		15	%
K_2	I_{OUT}/I_{SENSE}	$I_{OUT} = 0.8\text{ A}, V_{SENSE} = 2\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1372	1730	2058	
$dK_2/K_2^{(1)}$	Current sense ratio drift	$I_{OUT} = 0.8\text{ A}, V_{SENSE} = 2\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-12		12	%
K_3	I_{OUT}/I_{SENSE}	$I_{OUT} = 1.6\text{ A}, V_{SENSE} = 2\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1509	1720	1921	
$dK_3/K_3^{(1)}$	Current sense ratio drift	$I_{OUT} = 1.6\text{ A}, V_{SENSE} = 2\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-8		8	%
K_4	I_{OUT}/I_{SENSE}	$I_{OUT} = 6\text{ A}, V_{SENSE} = 4\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	1646	1720	1784	
$dK_4/K_4^{(1)}$	Current sense ratio drift	$I_{OUT} = 6\text{ A}, V_{SENSE} = 4\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	-4		4	%
I_{SENSE0}	Analog sense leakage current	$I_{OUT} = 0\text{ A}, V_{SENSE} = 0\text{ V}, V_{IN} = 0\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	0		1	μA
		$I_{OUT} = 0\text{ A}, V_{SENSE} = 0\text{ V}, V_{IN} = 5\text{ V}, T_J = -40\text{ °C to }150\text{ °C}$	0		2	

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SENSE}	Max analog sense output voltage	$I_{OUT} = 6\text{ A}$, $R_{SENSE} = 3.9\text{ k}\Omega$	5			V
V_{SENSEH}	Analog sense output voltage in fault condition ⁽²⁾	$V_{CC} = 24\text{ V}$, $R_{SENSE} = 3.9\text{ k}\Omega$	7.5	8.5	9.5	V
I_{SENSEH}	Analog sense output current in fault condition ⁽²⁾	$V_{CC} = 24\text{ V}$, $V_{SENSE} = 5\text{ V}$	4.9	9	12	mA
$t_{DSENSE2H}$	Delay response time from rising edge of INPUT pins	$V_{SENSE} < 4\text{ V}$, $0.07\text{ A} < I_{OUT} < 6\text{ A}$, $I_{SENSE} = 90\%$ of $I_{SENSEMAX}$, (see Figure 7)		100	200	μs
$\Delta t_{DSENSE2H}$	Delay response time between rising edge of output current and rising edge of current sense	$V_{SENSE} < 4\text{ V}$, $I_{SENSE} = 90\%$ of $I_{SENSEMAX}$, $I_{OUT} = 90\%$ of I_{OUTMAX} , $I_{OUTMAX} = 1.5\text{ A}$ (see Figure 11)			150	μs
$t_{DSENSE2L}$	Delay response time from falling edge of INPUT pins	$V_{SENSE} < 4\text{ V}$, $0.07\text{ A} < I_{OUT} < 6\text{ A}$, $I_{SENSE} = 10\%$ of $I_{SENSEMAX}$, (see Figure 7)		5	20	μs

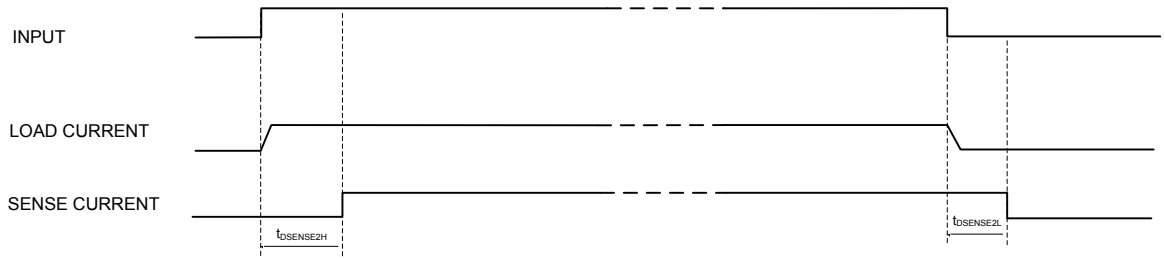
1. Specified by design, not tested in production.

2. Fault condition includes: power limitation, overtemperature and openload in off-state condition.

Table 10. Openload detection ($V_{FR_Stby} = 5\text{ V}$)

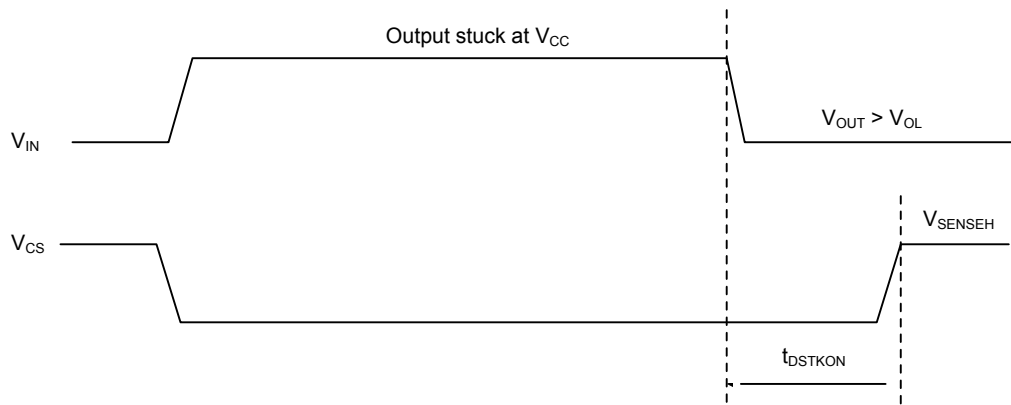
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{OL}	Openload off-state voltage detection threshold	$V_{IN} = 0\text{ V}$, $8\text{ V} < V_{CC} < 36\text{ V}$ $V_{FR_Stby} = 5\text{ V}$	2	-	4	V
t_{DSTKON}	Output short circuit to V_{CC} detection delay at turn off	$V_{FR_Stby} = 5\text{ V}$ (see Figure 8)	180	-	1800	μs
$I_{L(off2)}$	Off-state output current at $V_{OUT} = 4\text{ V}$	$V_{IN} = 0\text{ V}$, $V_{SENSE} = 0\text{ V}$, V_{OUT} rising from 0 V to 4 V $V_{FR_Stby} = 5\text{ V}$	-120	-	0	μA
t_{d_vol}	Delay response from output rising edge to V_{SENSE} rising edge in openload	$V_{OUT} = 4\text{ V}$, $V_{IN} = 0\text{ V}$, $V_{SENSE} = 90\%$ of V_{SENSEH} , $R_{SENSE} = 3.9\text{ k}\Omega$ $V_{FR_Stby} = 5\text{ V}$		-	20	μs
t_{DFRSTK_ON}	Output short circuit to V_{CC} detection delay at FR_Stby activation	Input1, 2 = low (see Figure 10)		-	50	μs

Figure 7. Current sense delay characteristics



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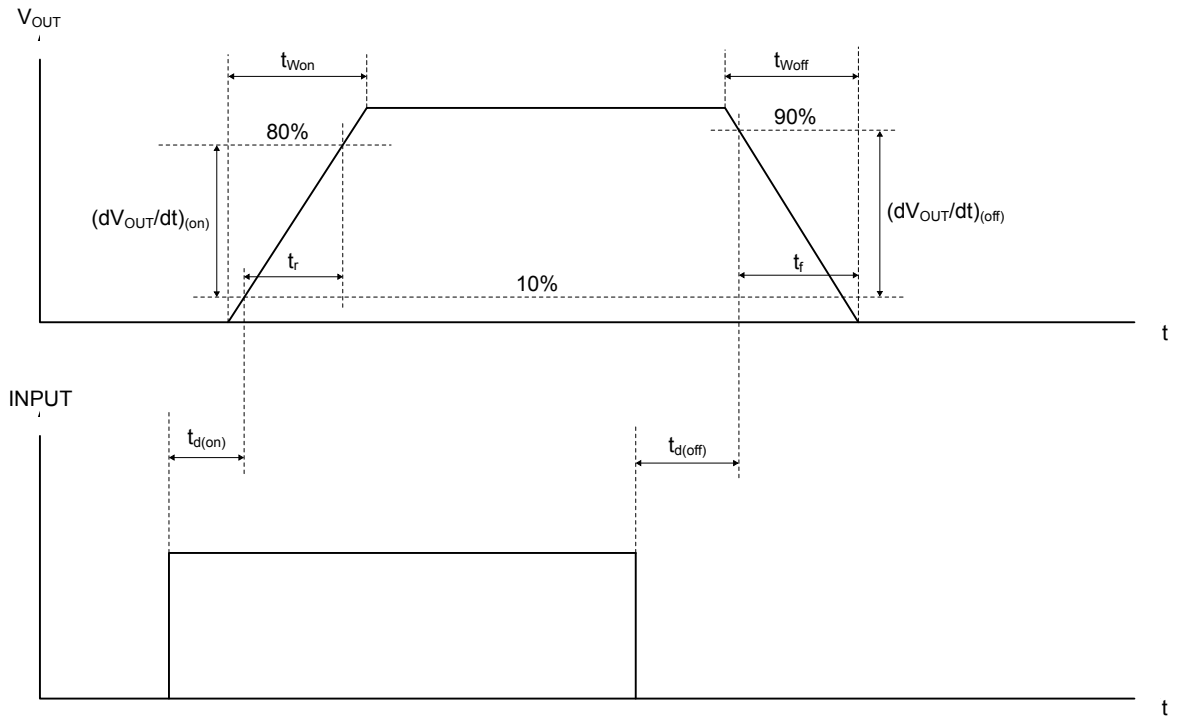
Figure 8. Openload off-state delay timing



NOTE: $V_{\text{FR_stby}} = 5 \text{ V}$.

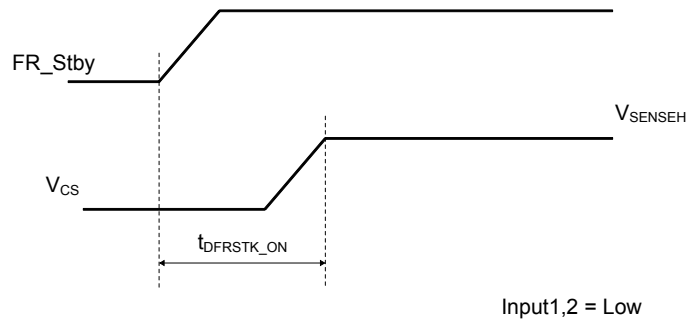
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Figure 9. Switching characteristics



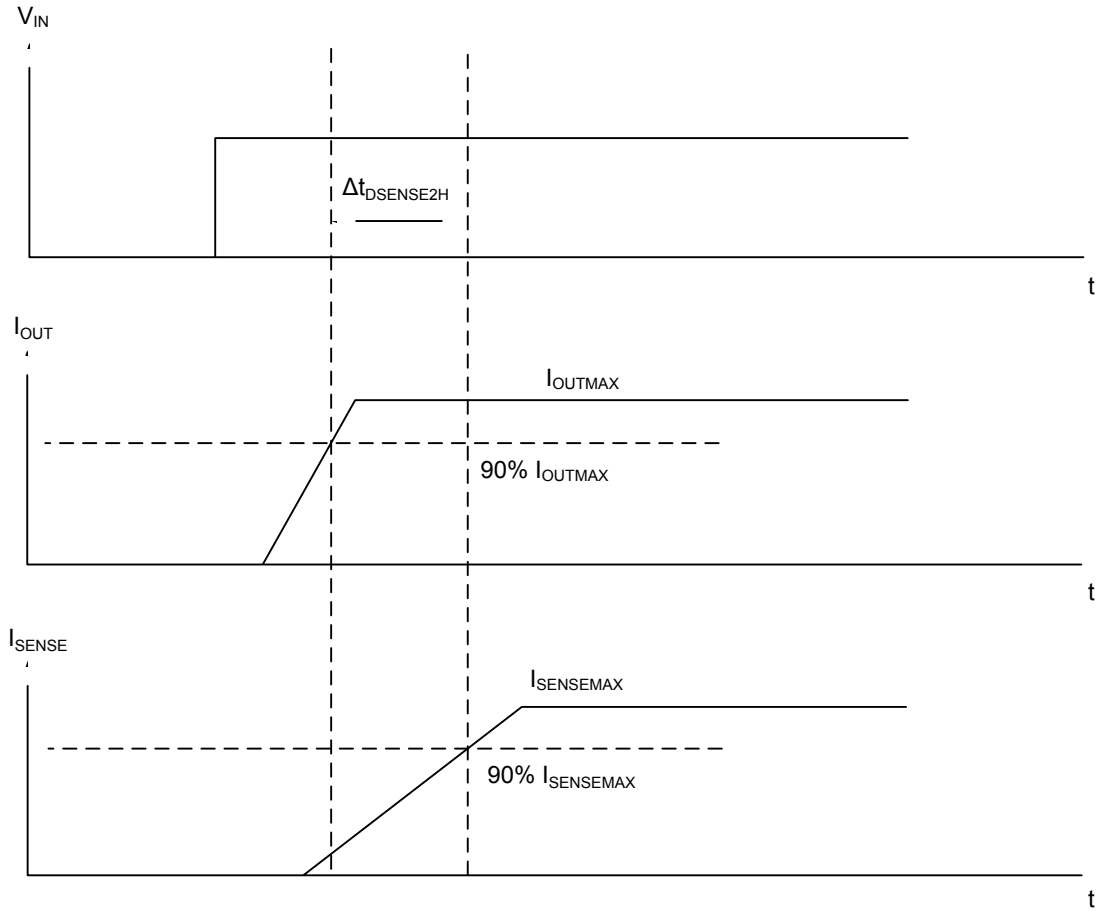
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Figure 10. Output stuck to V_{CC} detection delay time at FR_Stby activation



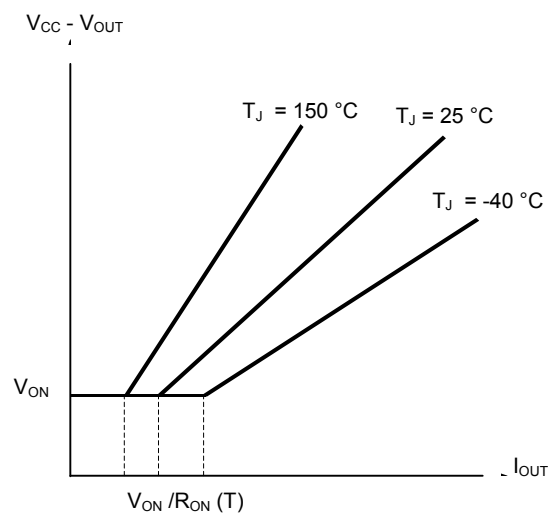
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Figure 11. Delay response time between rising edge of output current and rising edge of current sense

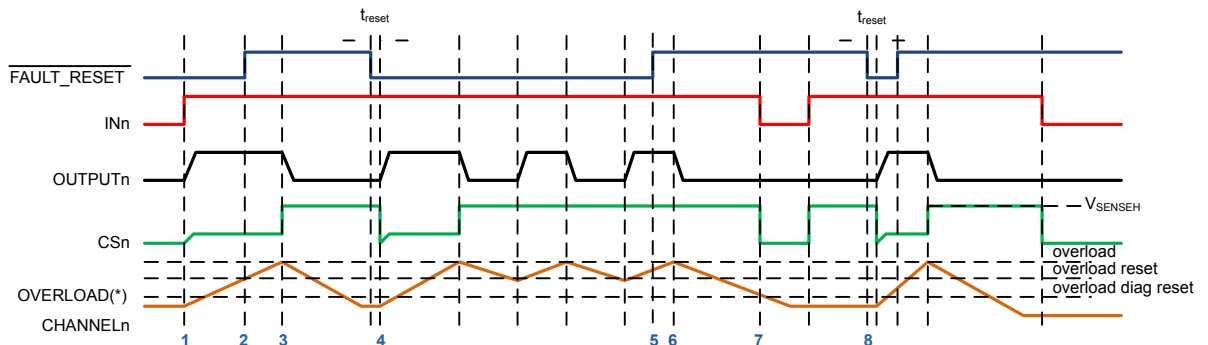


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Figure 12. Output voltage drop limitation



AG00074V1

Figure 13. Device behavior in overload condition


- 1: OUTPUTn and CSn controlled by INn
- 2: FAULT_RESET from '0' to '1' → no action on CSn pin
- 3: overload latch-off. INn high → CSn high
- 4: FAULT_RESET low AND Temp channeln < overload_reset → overload latch reset after t_reset
- 4 to 5: FAULT_RESET low AND INn high → thermal cycling, CSn high
- 5: FAULT_RESET high → latch-off reset disabled
- 6 to 7: overload event and FAULT_RESET high → latch-off, no thermal cycling
- 7 to 8: overload diagnostic disabled/enabled by the input
- 8: overload latch-off reset by FAULT_RESET

(*) OVERLOAD = thermal shutdown OR power limitation

GAPGCF000116_v2

Table 11. Truth table

Conditions	Fault reset standby	Input	Output	Sense
Standby	L	L	L	0
Normal operation	X	L	L	0
	X	H	H	Nominal
Overload	X	L	L	0
	X	H	H	> Nominal
Overtemperature/short to ground	X	L	L	0
	L	H	Cycling	V _{SENSEH}
	H	H	Latched	V _{SENSEH}
Undervoltage	X	X	L	0
Short to V _{BAT}	L	L	H	0
	H	L	H	V _{SENSEH}
	X	H	H	< Nominal
Openload off-state (with pull-up)	L	L	H	0
	H	L	H	V _{SENSEH}
	X	H	H	0
Negative output voltage clamp	X	L	Negative	0

Table 12. Electrical transient requirements (part 1)

ISO 7637-2: 2004 (E) Test pulse	Test levels ⁽¹⁾		Number of pulses or test times	Burst cycle/pulse repetition time		Delays and impedence
	III	IV				
1	-450 V	-600 V	5000 pulses	0.5 s	5 s	1 ms, 50 Ω
2a	37 V	50 V	5000 pulses	0.2 s	5 s	50 μs, 2 Ω
3a	- 150 V	- 200 V	1 h	90 ms	100 ms	0.1 μs, 50 Ω
3b	+ 150 V	+ 200 V	1 h	90 ms	100 ms	0.1 μs, 50 Ω
4	- 12 V	- 16 V	1 pulse			100 ms, 0.01 Ω
5b ⁽²⁾	+ 123 V	+ 174 V	1 pulse			350 ms, 1 Ω

1. The above test levels must be considered referred to $V_{CC} = 24.5$ V except for pulse 5b.
2. Valid in case of external load dump clamp: 58 V maximum referred to ground.

Table 13. Electrical transient requirements (part 2)

ISO 7637-2: 2004 (E) Test pulse	Test level results	
	III	IV
1	C	C
2a	C	C
3a	C	C
3b ⁽¹⁾	E	E
3b ⁽²⁾	C	C
4	C	C
5b ⁽³⁾	C	C

1. Without capacitor between V_{CC} and GND.
2. With 10 nF between V_{CC} and GND.
3. External load dump clamp, 58 V maximum, referred to ground.

Table 14. Electrical transient requirements (part 3)

Class	Contents
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device are not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.

2.4 Electrical characteristics (curves)

Figure 14. Off-state output current

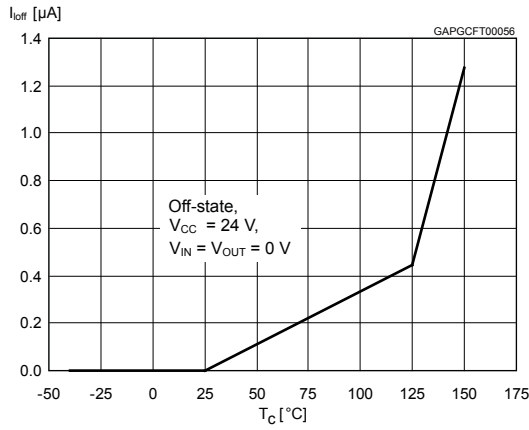


Figure 15. High level input current

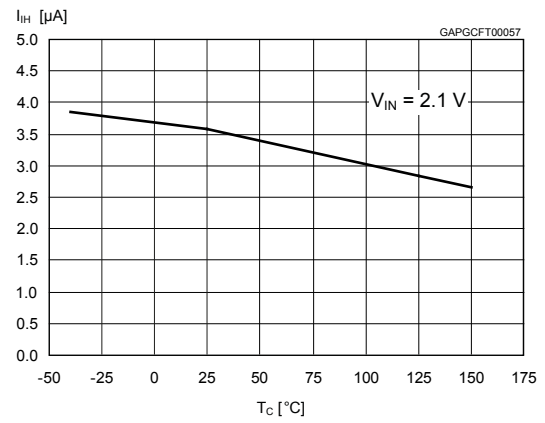


Figure 16. Input clamp voltage

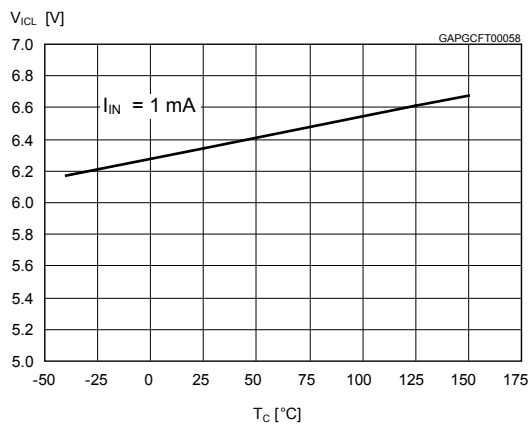


Figure 17. Low level input voltage

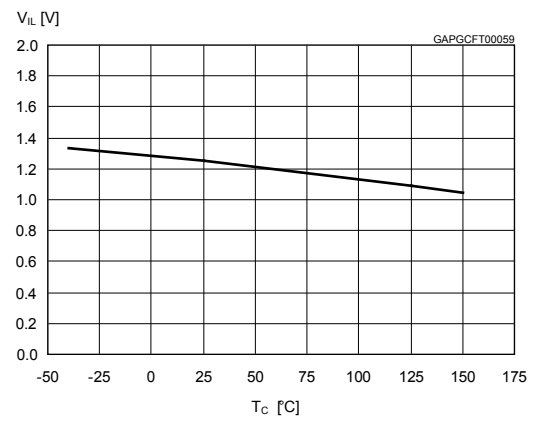


Figure 18. High level input voltage

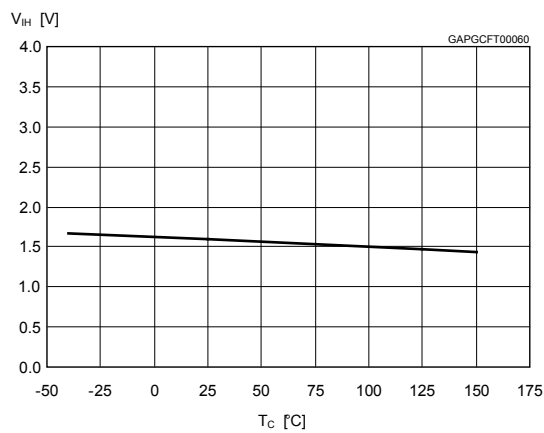


Figure 19. Input hysteresis voltage

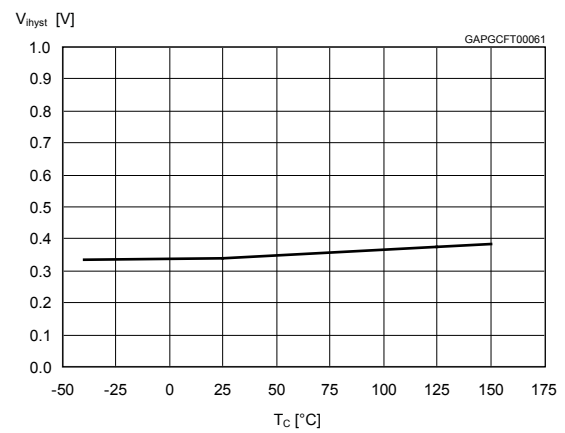


Figure 20. On-state resistance vs T_C

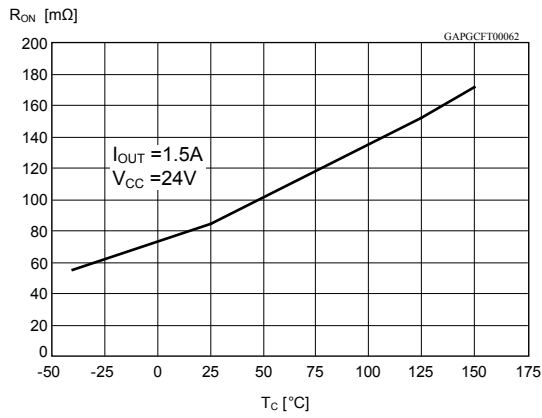


Figure 21. On-state resistance vs V_{CC}

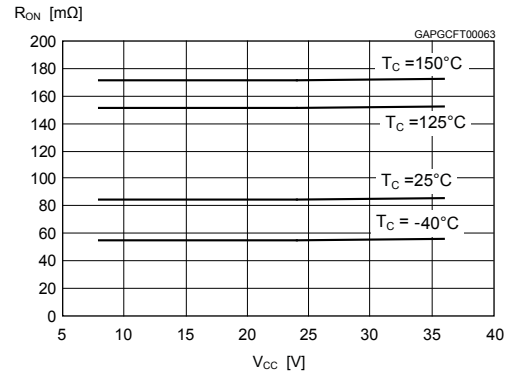


Figure 22. Turn-on voltage slope

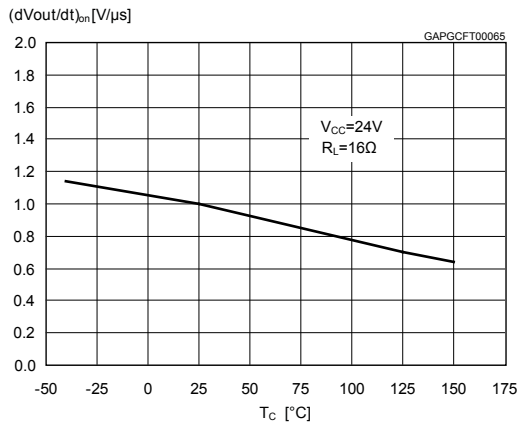


Figure 23. Turn-off voltage slope

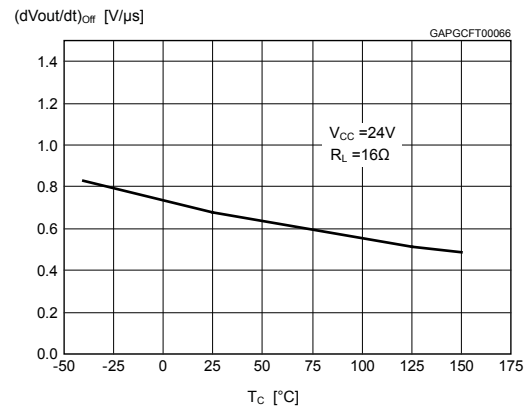
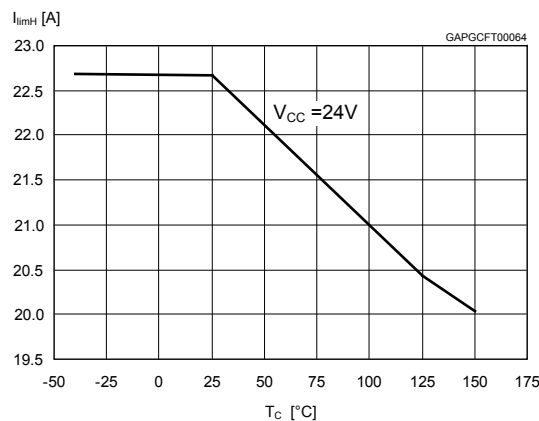
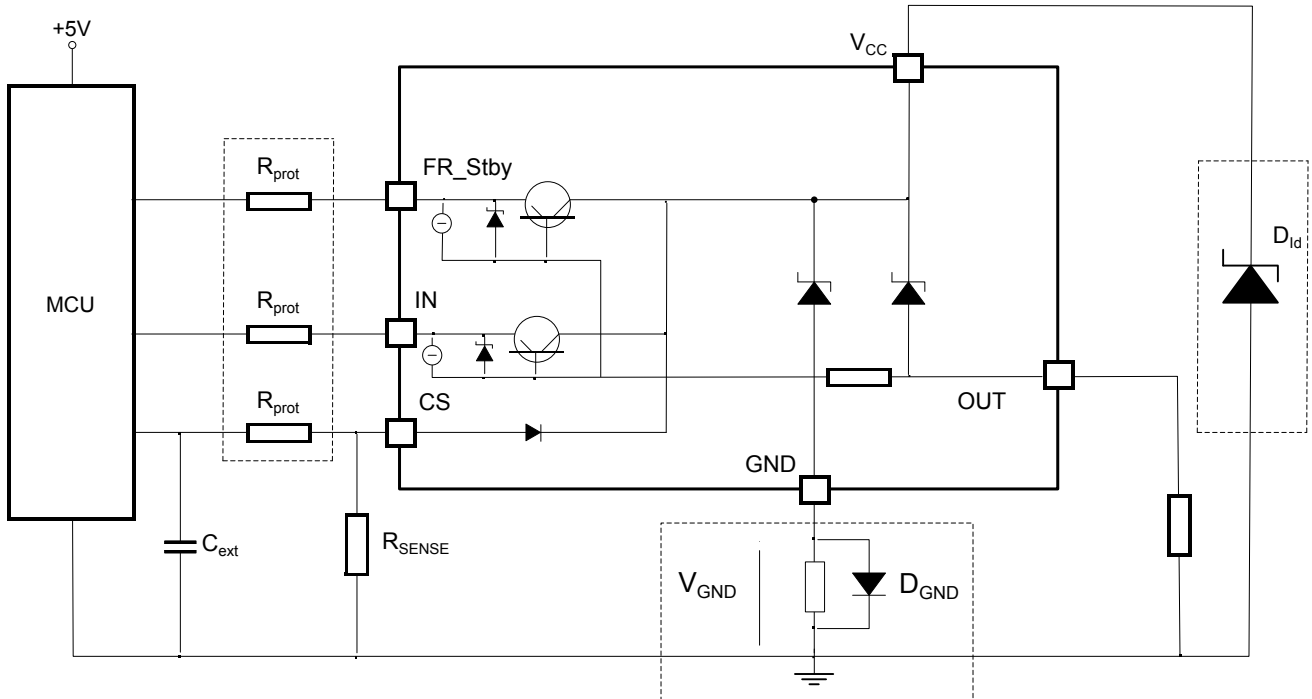


Figure 24. I_{LIMH} vs T_C



3 Application information

Figure 25. Application schematic



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3.1 GND protection network against reverse battery

3.1.1 Solution 1: resistor in the ground line (R_{GND} only)

This solution can be used with any load type.

The following is an indication on how to dimension the R_{GND} resistor.

1. $R_{GND} \leq 600 \text{ mV} / (I_{S(on)max.})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

Where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0 \text{ V}$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared among several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max.}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not shared by the device ground then the R_{GND} produces a shift ($I_{S(on)max.} \cdot R_{GND}$) in the input thresholds and the status output values. This shift varies depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor, then ST suggests solution 2 is used (see below).

3.1.2 Solution 2: diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 4.7 \text{ k}\Omega$) should be inserted in parallel to D_{GND} if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network produces a shift ($\approx 600 \text{ mV}$) in the input threshold and in the status output values, if the microprocessor ground is not common to the device ground. This shift does not vary if more than one HSD shares the same diode/resistor network.

3.2 Load dump protection

D_{ld} is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the V_{CC} maximum DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than the ones shown in the ISO 7637-2 2004 (E) [Table 12](#), [Table 13](#) and [Table 14](#).

3.3 MCU I/Os protection

If a ground protection network is used and negative transient is present on the V_{CC} line, the control pins are pulled negative. ST suggests that a resistor (R_{prot}) has to be inserted in line to prevent the microcontroller I/Os pins from latching-up.

The value of these resistors is a compromise between the leakage current of the microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

Equation: R_{prot} range calculation

$$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

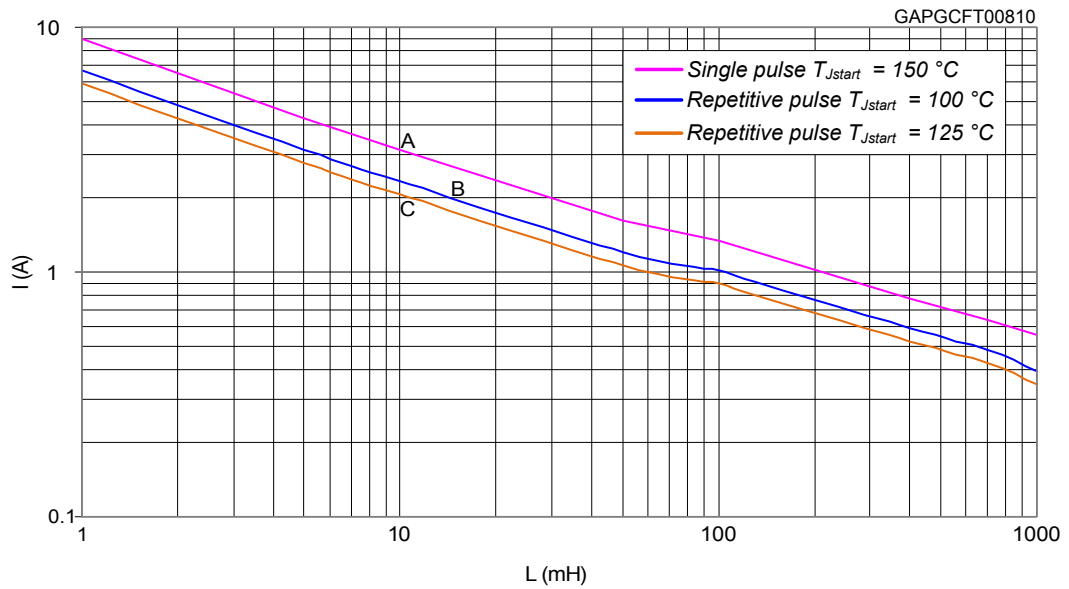
For $V_{CCpeak} = -600 \text{ V}$ and $I_{latchup} \geq 20 \text{ mA}$; $V_{OH\mu C} \geq 4.5 \text{ V}$

$30 \text{ k}\Omega \leq R_{prot} \leq 180 \text{ k}\Omega$.

Recommended value: $R_{prot} = 60 \text{ k}\Omega$.

4 Maximum demagnetization energy (V_{CC} = 24 V)

Figure 26. Maximum turn off current versus inductance

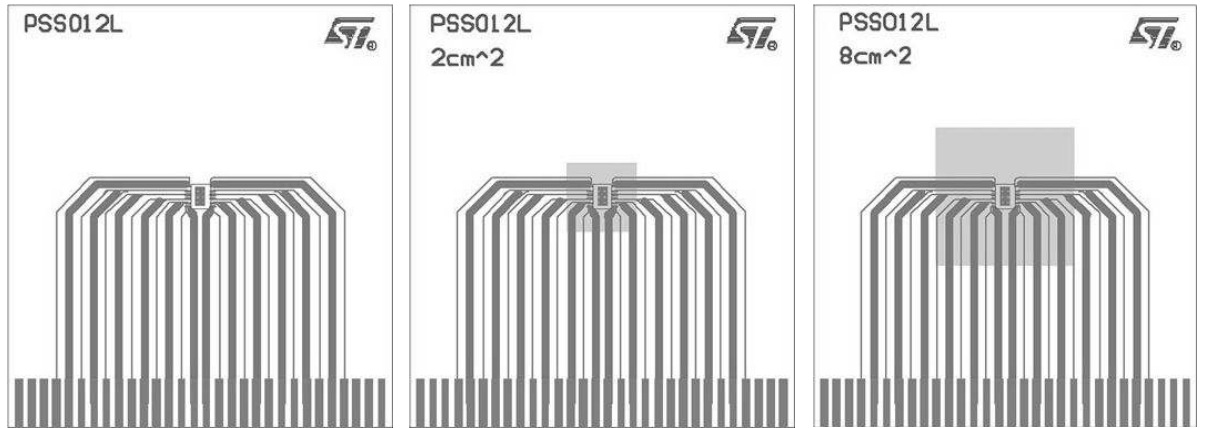


Note: Values are generated with $R_L = 0\ \Omega$. In case of repetitive pulses, T_{Jstart} (at the beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

5 Package and PCB thermal data

5.1 PowerSSO-12 thermal data

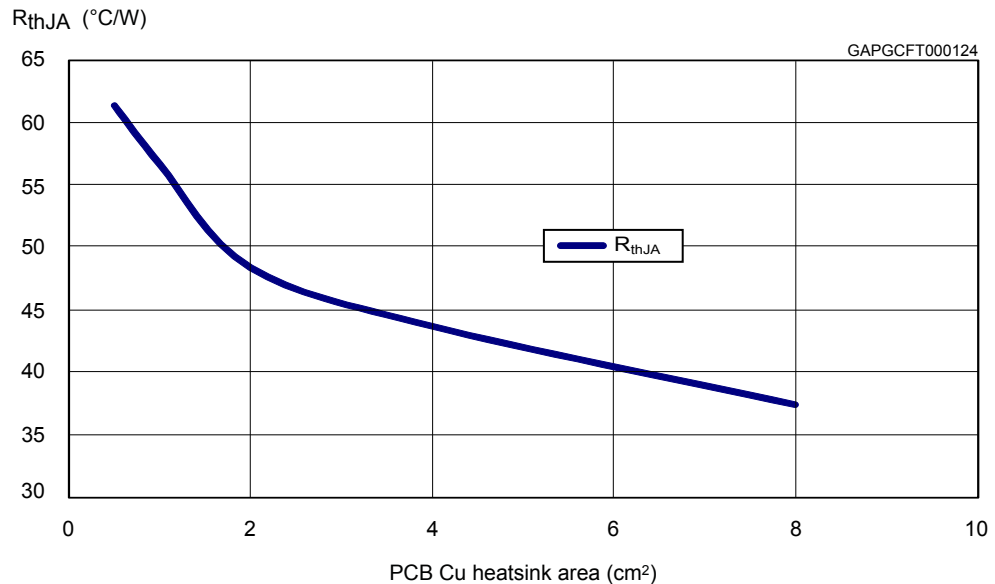
Figure 27. PowerSSO-12 PCB



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Layout condition of R_{th} and Z_{th} measurements (board finish thickness 1.6 mm \pm 10%; board double layer; board dimension 77 mm x 86 mm; board material FR4; Cu thickness 0.070 mm (front and back side); thermal vias separation 1.2 mm; thermal via diameter 0.3 mm \pm 0.08 mm; Cu thickness on vias 0.025 mm; footprint dimension 4.1 mm x 6.5 mm).

Figure 28. R_{thJA} vs PCB copper area in open box free air condition (one channel ON)



GAPGCF000124

Figure 29. PowerSSO-12 thermal impedance junction ambient single pulse (one channel ON)

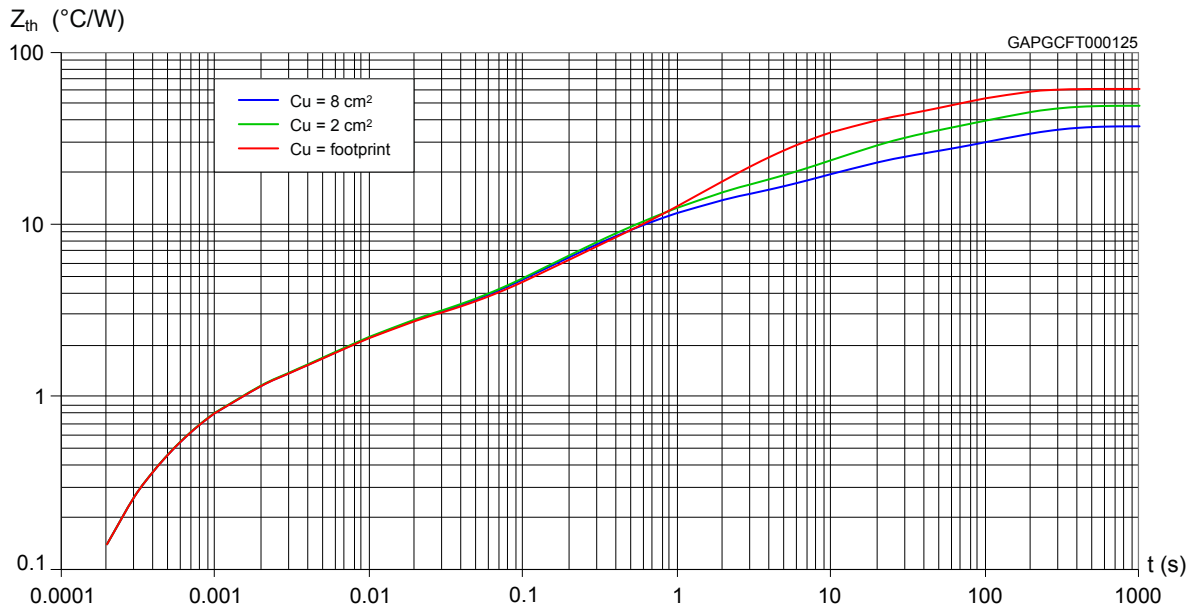
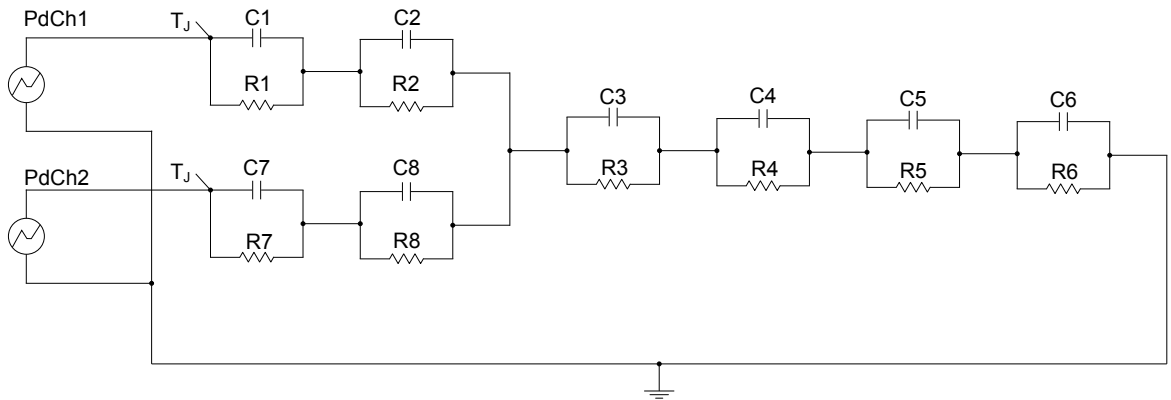


Figure 30. Thermal fitting model of a double channel HSD in PowerSSO-12



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The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered.

Equation: pulse calculation formula

$$Z_{th\delta} = R_{th} \cdot \delta + Z_{thp} (1 - \delta)$$

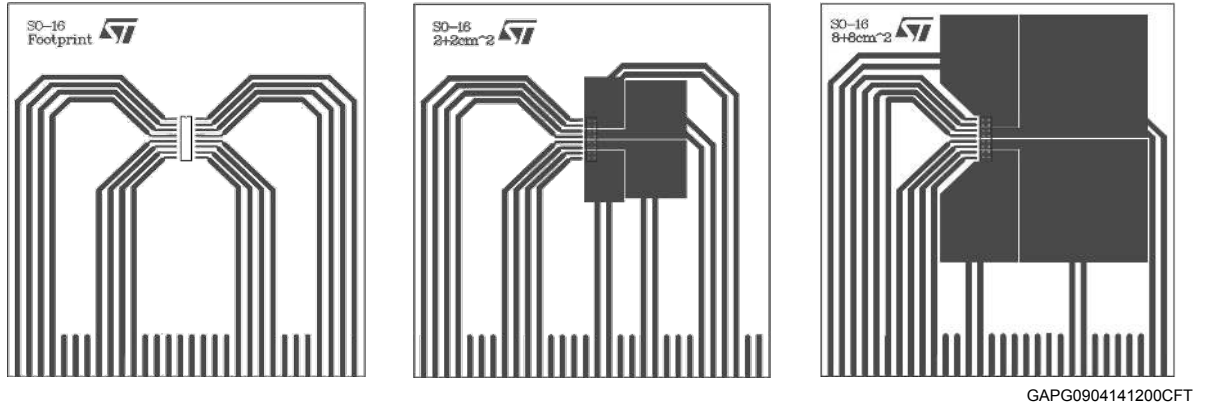
Where $\delta = t_p/T$

Table 15. Thermal parameters

Area/island (cm ²)	Footprint	2	8
R1 = R7 (°C/W)	0.8		
R2 = R8 (°C/W)	1.5		
R3 (°C/W)	3		
R4 (°C/W)	8	8	7
R5 (°C/W)	22	15	10
R6 (°C/W)	26	20	15
C1 = C7 (W.s/°C)	0.0008		
C2 = C8 (W.s/°C)	0.005		
C3 (W.s/°C)	0.05		
C4 (W.s/°C)	0.2	0.1	0.1
C5 (W.s/°C)	0.27	0.8	1
C6 (W.s/°C)	3	6	9

5.2 SO-16N thermal data

Figure 31. SO-16N PCB



Layout condition of R_{th} and Z_{th} measurements (board finish thickness 1.6 mm \pm 10%; board double layer; board dimension 129 mm x 60 mm; board material FR4; Cu thickness 0.070 mm (front and back side); thermal vias separation 1.2 mm; thermal via diameter 0.3 mm \pm 0.08 mm; Cu thickness on vias 0.025 mm).

Figure 32. R_{thJA} vs PCB copper area in open box free air condition (one channel ON)

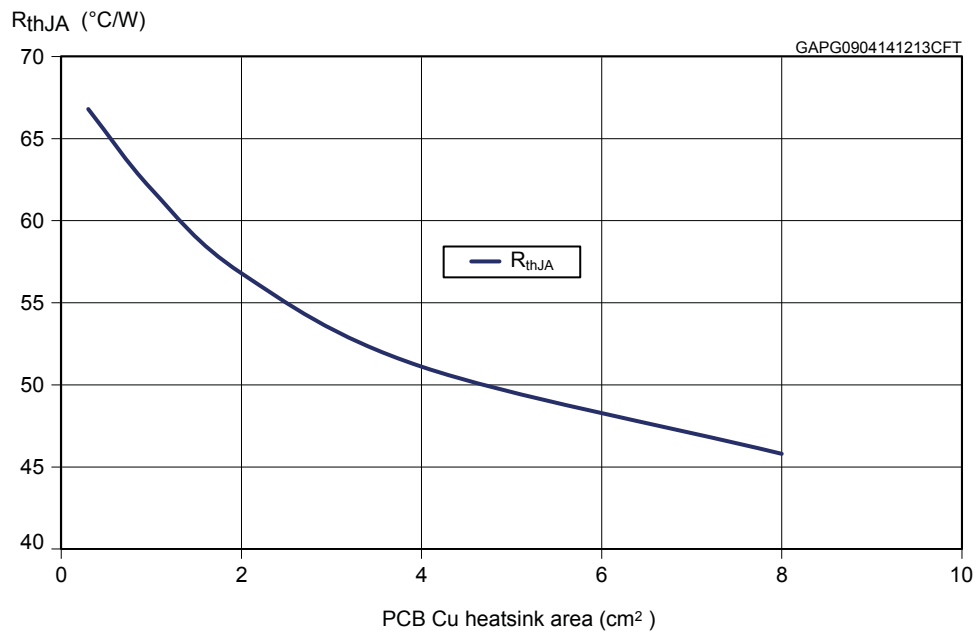


Figure 33. SO-16N thermal impedance junction ambient single pulse (one channel ON)

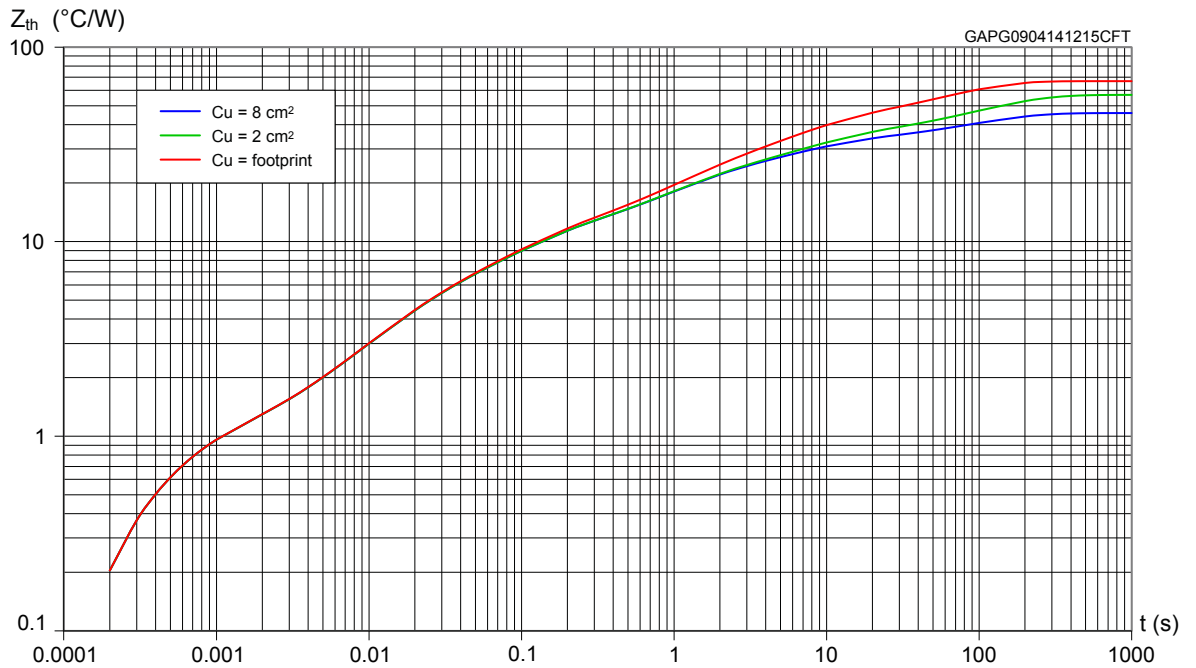
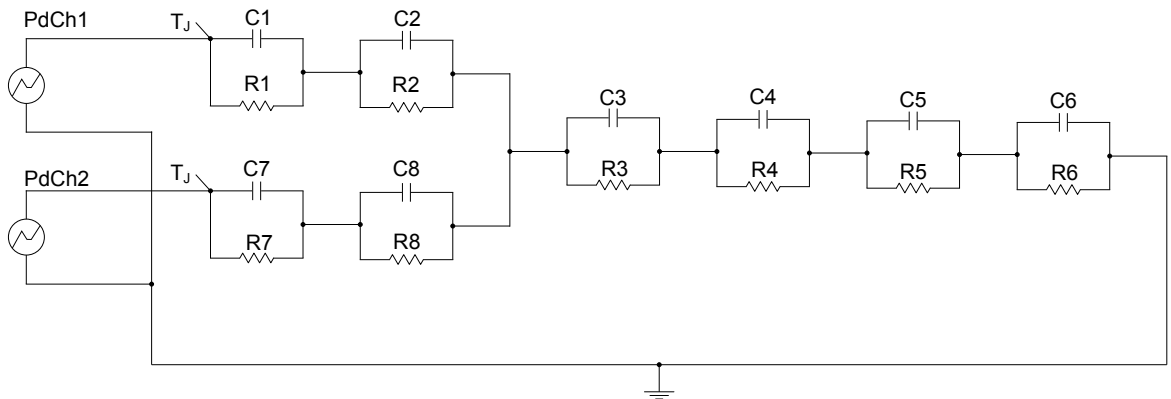


Figure 34. Thermal fitting model of a double channel HSD in SO-16N



GAPGCFT00438

The fitting model is a simplified thermal tool and is valid for transient evolutions where the embedded protections (power limitation or thermal cycling during thermal shutdown) are not triggered.

Equation: pulse calculation formula

$$Z_{th\bar{\delta}} = R_{th} \cdot \bar{\delta} + Z_{thp} (1 - \bar{\delta})$$

Where $\bar{\delta} = t_p/T$

Table 16. Thermal parameters

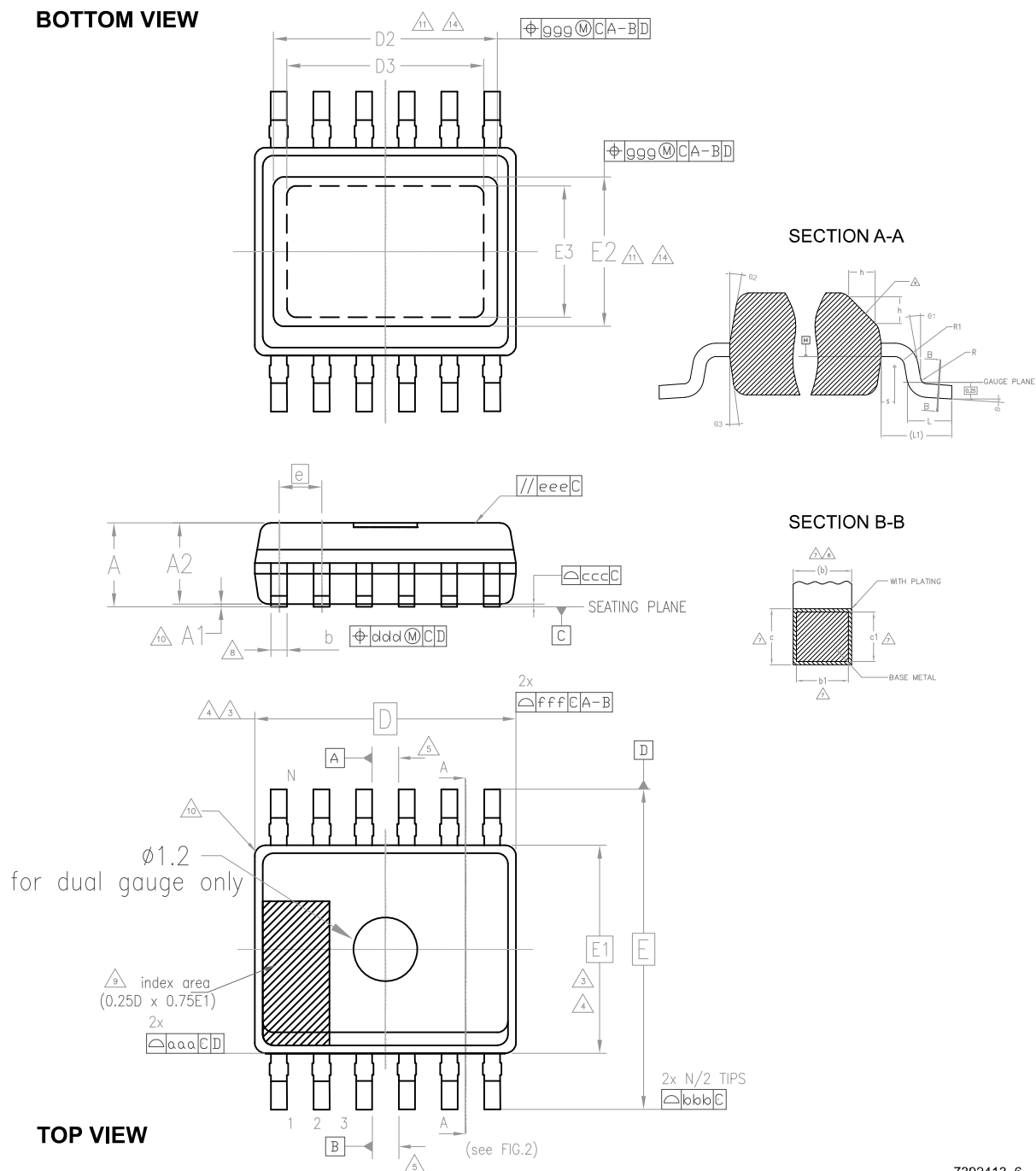
Area/island (cm ²)	Footprint	2	8
R1 = R7 (°C/W)	0.8		
R2 = R8 (°C/W)	3		
R3 (°C/W)	6		
R4 (°C/W)	10		
R5 (°C/W)	20	14	12
R6 (°C/W)	27	23	14
C1 = C7 (W.s/°C)	0.0005		
C2 = C8 (W.s/°C)	0.005		
C3 (W.s/°C)	0.015		
C4 (W.s/°C)	0.1		
C5 (W.s/°C)	0.3	0.5	0.5
C6 (W.s/°C)	2.5	5	7

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

6.1 PowerSSO-12 package information

Figure 35. PowerSSO-12 package dimensions



7392413_6

Table 17. PowerSSO-12 mechanical data

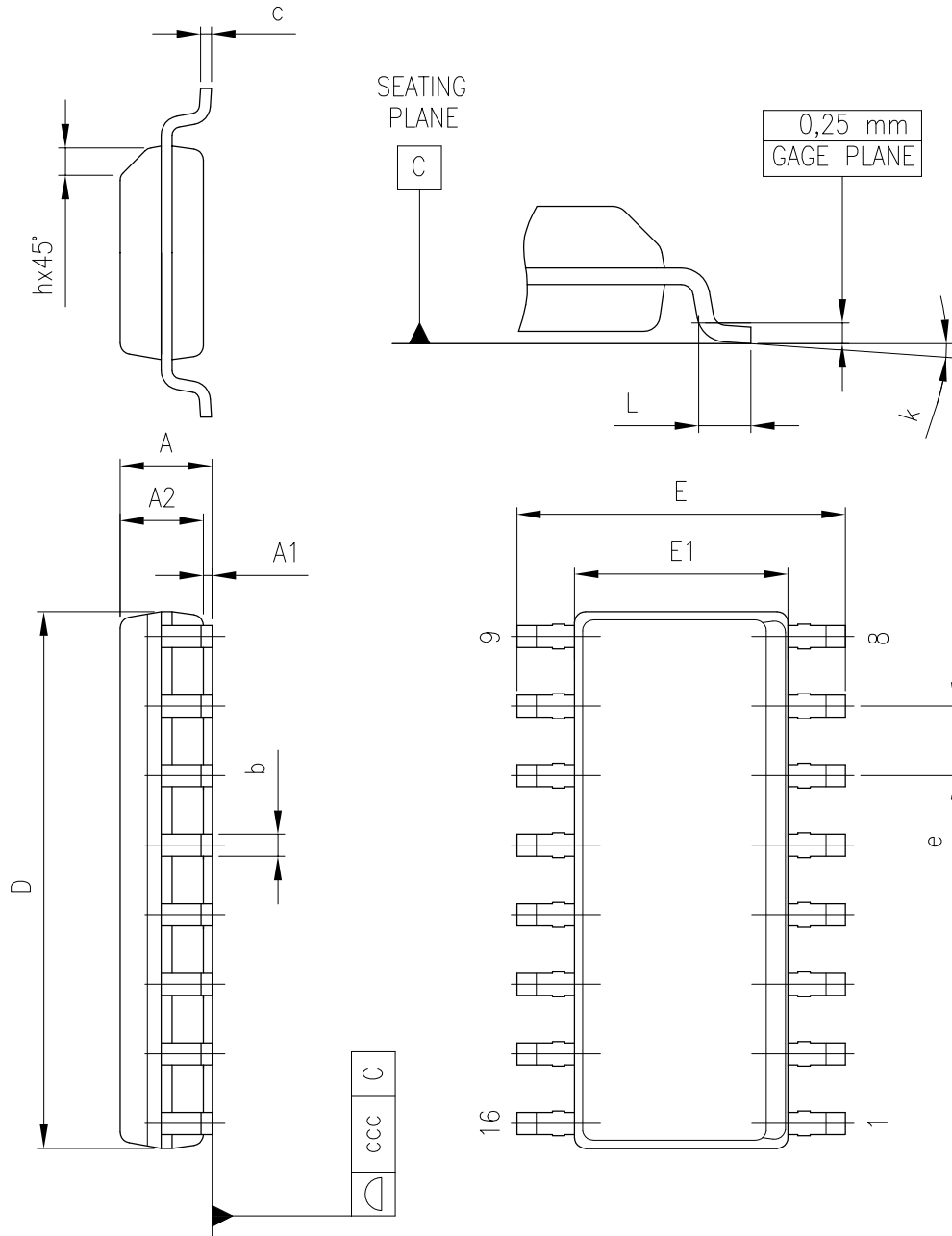
Symbol	Millimeters		
	Min.	Typ.	Max.
θ	0°		8°
θ_1	0°		
θ_2	5°		15°
θ_3	5°		15°
A	1.25		1.70
A1	0.00		0.10
A2	1.10		1.60
b	0.23		0.41
b1	0.20	0.25	0.39
c	0.19		0.25
c1	0.19	0.20	0.23
D	4.90 BSC		
D2	3.60		4.20
D3	2.90		
e	0.80 BSC		
E	6.00 BSC		
E1	3.90 BSC		
E2	1.90		2.50
E3	1.20		
h	0.25		0.50
L	0.40		1.27
L1	1.00 REF		
N	12		
R	0.07		
R1	0.07		
S	0.20		

Table 18. PowerSSO-12 tolerance of form and position

Symbol	Millimeters
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.08
eee	0.10
fff	0.10
ggg	0.15

6.2 SO-16 narrow package information

Figure 36. SO-16 narrow package dimensions



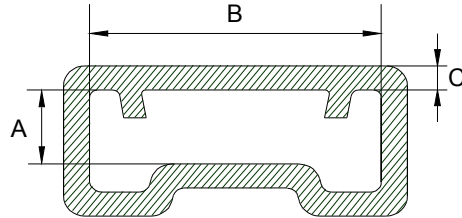
0016020_10

Table 19. SO-16 narrow mechanical data

Symbol	Millimeters		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		1.60
b	0.31		0.51
c	0.17		0.25
D	9.80	9.90	10.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
k	0°		8°
ccc			0.10

6.3 PowerSSO-12 packing information

Figure 37. PowerSSO-12 tube shipment (no suffix)

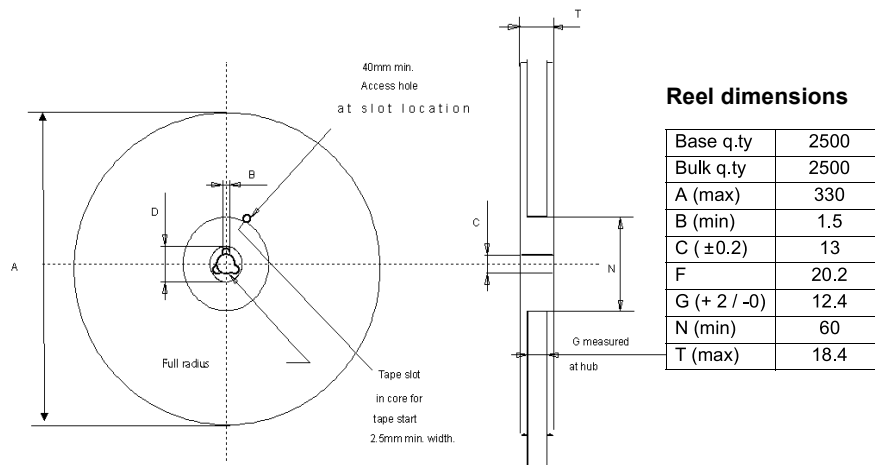


All dimensions are in mm.

Base q.ty	100
Bulk q.ty	2000
Tube length (± 0.5)	532
A	1.85
B	6.75
C (± 0.1)	0.6

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Figure 38. PowerSSO-12 tape and reel shipment (suffix "TR")



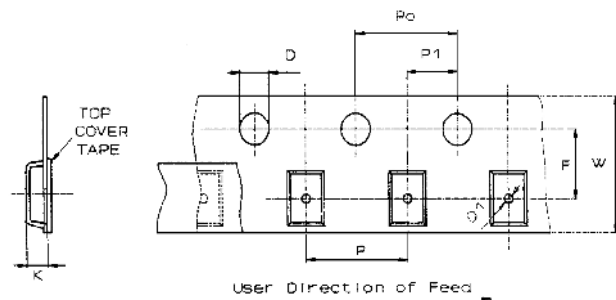
Reel dimensions

Base q.ty	2500
Bulk q.ty	2500
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+2 / -0)	12.4
N (min)	60
T (max)	18.4

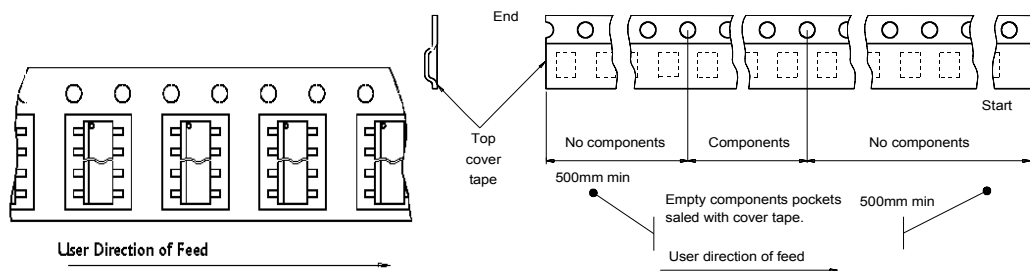
Tape dimensions

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb. 1986

Tape width	W	12
Tape hole spacing	P0 (± 0.1)	4
Component spacing	P	8
Hole diameter	D (± 0.05)	1.5
Hole diameter	D1 (min)	1.5
Hole position	F (± 0.1)	5.5
Compartment depth	K (max)	4.5
Hole spacing	P1 (± 0.1)	2

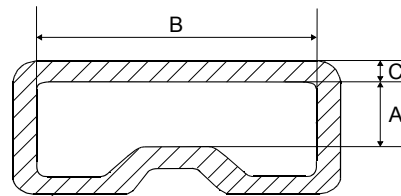


All dimensions are in mm.



6.4 SO-16N packing information

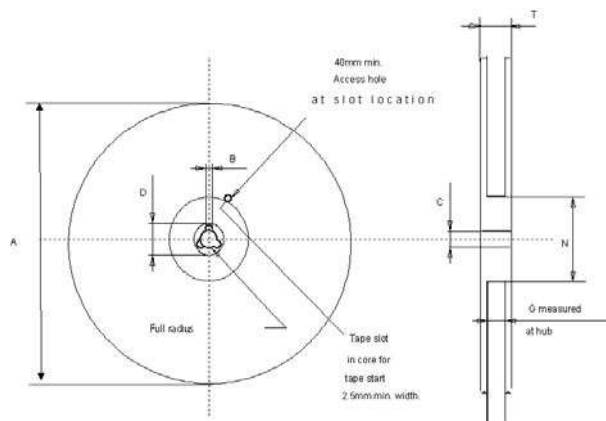
Figure 39. SO-16N tube shipment (no suffix)



Base q.ty	50
Bulk q.ty	1000
Tube length (± 0.5)	532
A	3.2
B	6
C (± 0.1)	0.6

All dimensions are in mm.

Figure 40. SO-16N tape and reel shipment (suffix "TR")



REEL DIMENSIONS

Base q.ty	1000
Bulk q.ty	1000
A (max.)	330
B (min.)	1.5
C (± 0.2)	13
F	20.2
G (+2 / -0)	16.4
N (min.)	60
T (max.)	22.4

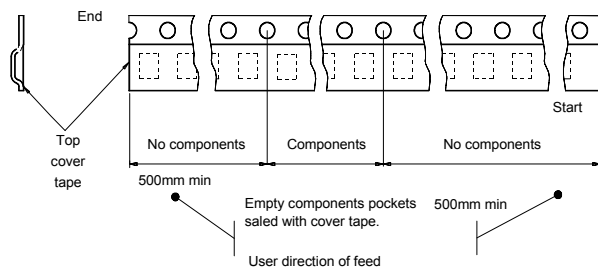
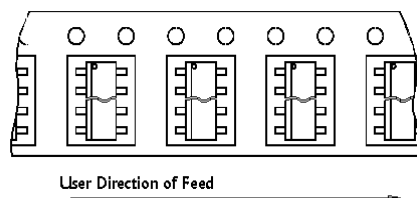
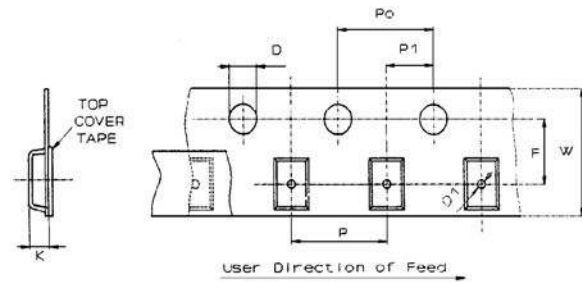
All dimensions are in mm.

TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	16
Tape hole spacing	P0 (± 0.1)	4
Component spacing	P	8
Hole diameter	D ($\pm 0.1/-0$)	1.5
Hole diameter	D1 (min.)	1.5
Hole position	F (± 0.05)	7.5
Compartment depth	K (max.)	6.5
Hole spacing	P1 (± 0.1)	2

All dimensions are in mm.



7 Order codes

Table 20. Device summary

Package	Order codes	
	Tube	Tape and reel
PowerSSO-12	VND5T100LAJ-E	VND5T100LAJTR-E
SO-16N	VND5T100LAS-E	VND5T100LASTR-E

Revision history

Table 21. Document revision history

Date	Revision	Changes
25-Jun-2012	1	Initial release.
18-Sep-2013	2	Disclaimer updated.
30-Apr-2014	3	Added SO-16N package and related details.
08-Feb-2016	4	<p><i>Table 4: Thermal data:</i></p> <ul style="list-style-type: none"> – Rthj-case: updated values – Rthj-pin: added row <p>Updated <i>Section 5.2: PowerSSO-12 mechanical data</i> and <i>Section 5.3: SO-16N package information</i></p>
23-Aug-2016	5	<p>Added indication of AEC-Q100 qualification in <i>Features</i>.</p> <p>Updated <i>Figure 3: Configuration diagram SO-16N (top view)</i>.</p>
16-Jun-2022	6	<p>Updated <i>PowerSSO-12 and SO-16N cover image</i>.</p> <p>Updated <i>Table 5. Power section</i>.</p> <p>Added notes in <i>Table 12. Electrical transient requirements (part 1)</i>.</p> <p>Updated <i>Figure 25. Application schematic</i>.</p> <p>Moved <i>Section 3.4: Maximum demagnetization energy (V_{CC} = 24 V)</i> to <i>Section 4 Maximum demagnetization energy (V_{CC} = 24 V)</i>.</p> <p>Updated <i>Section 6.1 PowerSSO-12 package information</i>.</p> <p>Removed <i>Packing information</i> chapter and moved related sections under <i>Section 6 Package information</i>.</p> <p>Minor text changes.</p>
21-Jul-2023	7	Updated <i>Figure 26. Maximum turn off current versus inductance</i> .

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